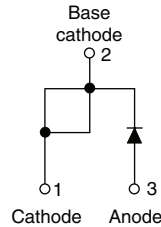


## Schottky Rectifier, 16 A



TO-220AC



### FEATURES

- 150 °C  $T_J$  operation
- Low forward voltage drop
- High frequency operation
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Guard ring for enhanced ruggedness and long term reliability
- Lead (Pb)-free (“PbF” suffix)
- Designed and qualified for industrial level



RoHS\*  
COMPLIANT

### PRODUCT SUMMARY

$I_{F(AV)}$	16 A
$V_R$	35/45 V
$V_F$ at 16 A at 25 °C	0.63 V
$I_{RM}$	40 mA at 125 °C

### DESCRIPTION

The MBR16..PbF Schottky rectifier has been optimized for low reverse leakage at high temperature. The proprietary barrier technology allows for reliable operation up to 150 °C junction temperature. Typical applications are in switching power supplies, converters, freewheeling diodes, and reverse battery protection.

### MAJOR RATINGS AND CHARACTERISTICS

SYMBOL	CHARACTERISTICS	VALUES	UNITS
$I_{F(AV)}$	Rectangular waveform	16	A
$V_{RRM}$		35/45	V
$I_{FSM}$	$t_p = 5 \mu s$ sine	1800	A
$V_F$	16 Apk, $T_J = 125 \text{ °C}$	0.57	V
$T_J$	Range	- 65 to 150	°C

### VOLTAGE RATINGS

PARAMETER	SYMBOL	MBR1635PbF	MBR1645PbF	UNITS
Maximum DC reverse voltage	$V_R$	35	45	V
Maximum working peak reverse voltage	$V_{RWM}$			

### ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum average forward current	$I_{F(AV)}$	$T_C = 134 \text{ °C}$ , rated $V_R$		16	A
Non-repetitive peak surge current	$I_{FSM}$	5 $\mu s$ sine or 3 $\mu s$ rect. pulse	Following any rated load condition and with rated $V_{RRM}$ applied	1800	A
		Surge applied at rated load condition half wave single phase, 60 Hz		150	
Non-repetitive avalanche energy	$E_{AS}$	$T_J = 25 \text{ °C}$ , $I_{AS} = 3.6 \text{ A}$ , $L = 3.7 \text{ mH}$		24	mJ
Repetitive avalanche current	$I_{AR}$	Current decaying linearly to zero in 1 $\mu s$ Frequency limited by $T_J$ maximum $V_A = 1.5 \times V_R$ typical		3.6	A

\* Pb containing terminations are not RoHS compliant, exemptions may apply

ELECTRICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum forward voltage drop	$V_{FM}^{(1)}$	16 A	$T_J = 25\text{ }^\circ\text{C}$	0.63	V
			$T_J = 125\text{ }^\circ\text{C}$	0.57	
Maximum instantaneous reverse current	$I_{RM}^{(1)}$	$T_J = 25\text{ }^\circ\text{C}$	Rated DC voltage	0.2	mA
		$T_J = 125\text{ }^\circ\text{C}$		40	
Maximum junction capacitance	$C_T$	$V_R = 5\text{ }V_{DC}$ (test signal range 100 kHz to 1 MHz) 25 °C		1400	pF
Typical series inductance	$L_S$	Measured from top of terminal to mounting plane		8.0	nH
Maximum voltage rate of change	dV/dt	Rated $V_R$		10 000	V/ $\mu$ s

**Note**

(1) Pulse width < 300  $\mu$ s, duty cycle < 2 %

THERMAL - MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum junction temperature range	$T_J$			- 65 to 150	$^\circ\text{C}$
Maximum storage temperature range	$T_{Stg}$			- 65 to 175	
Maximum thermal resistance, junction to case	$R_{thJC}$	DC operation		1.50	$^\circ\text{C/W}$
Typical thermal resistance, case to heatsink	$R_{thCS}$	Mounting surface, smooth and greased		0.50	
Approximate weight				2	g
				0.07	oz.
Mounting torque	minimum			6 (5)	kgf · cm (lbf · in)
	maximum			12 (10)	
Marking device		Case style TO-220AC (JEDEC)		MBR1635	
				MBR1645	

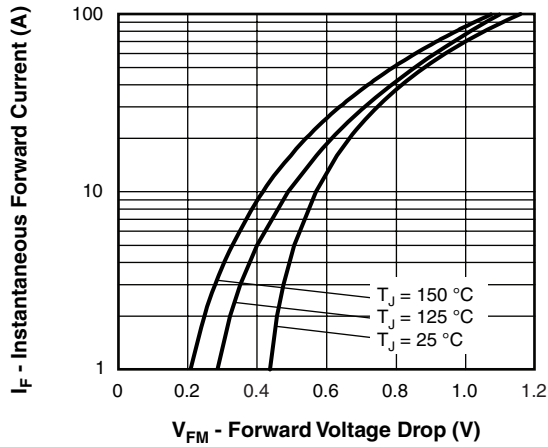


Fig. 1 - Maximum Forward Voltage Drop Characteristics

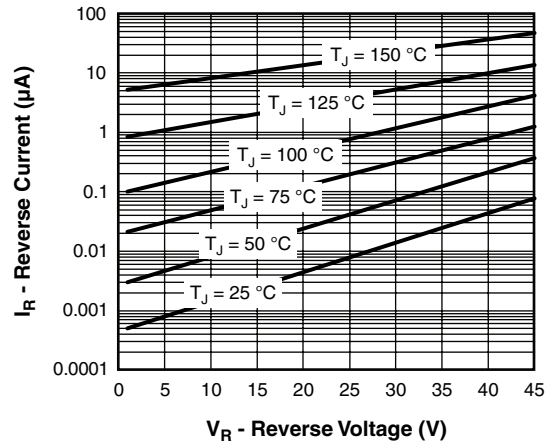


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

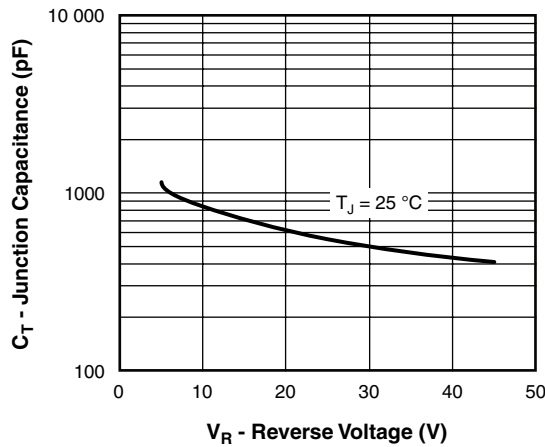


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

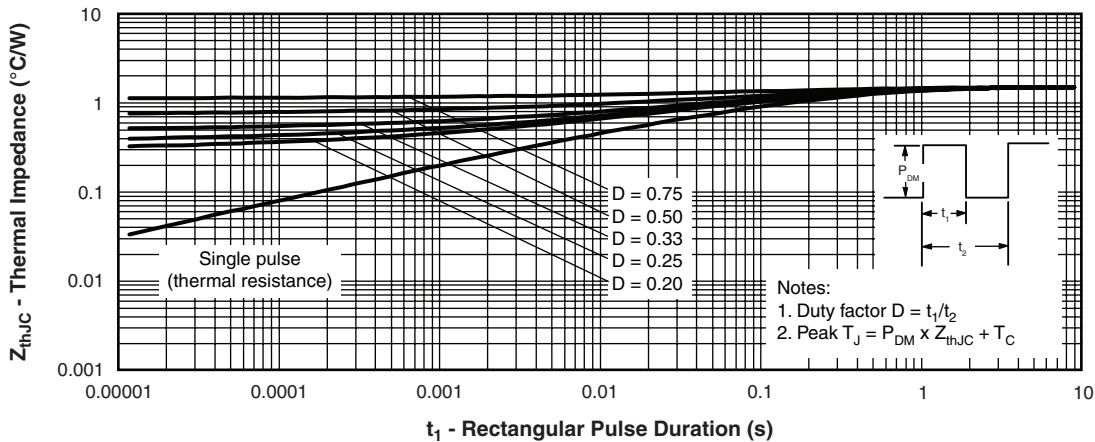


Fig. 4 - Maximum Thermal Impedance  $Z_{thJC}$  Characteristics

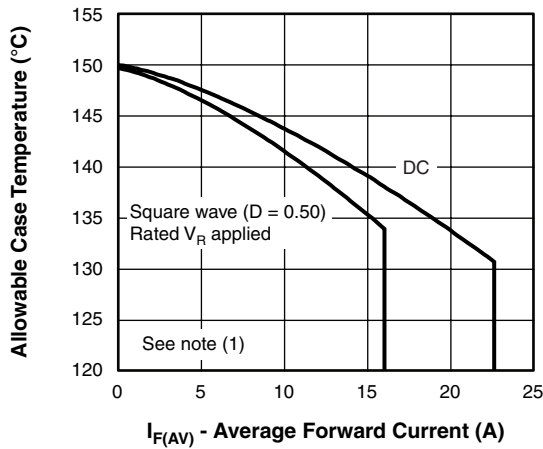


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

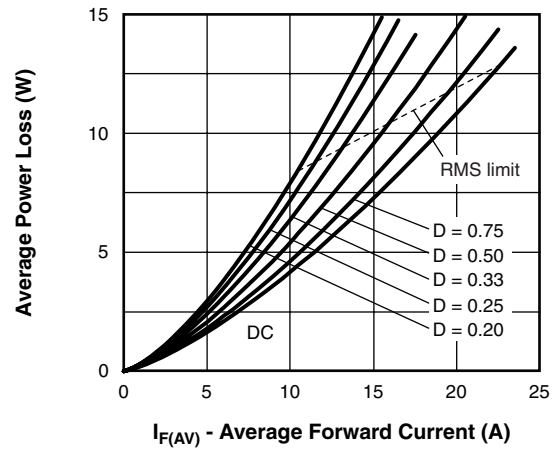


Fig. 6 - Forward Power Loss Characteristics

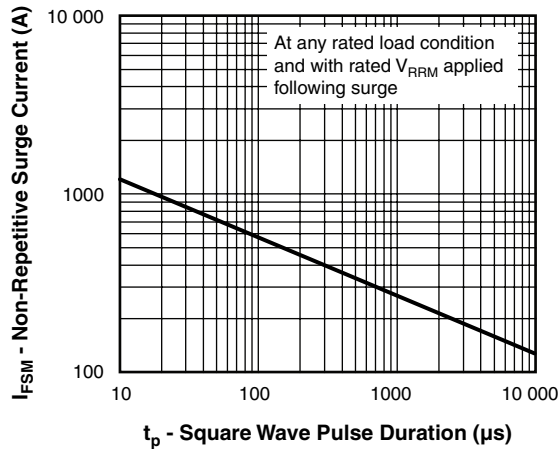


Fig. 7 - Maximum Non-Repetitive Surge Current (Per Leg)

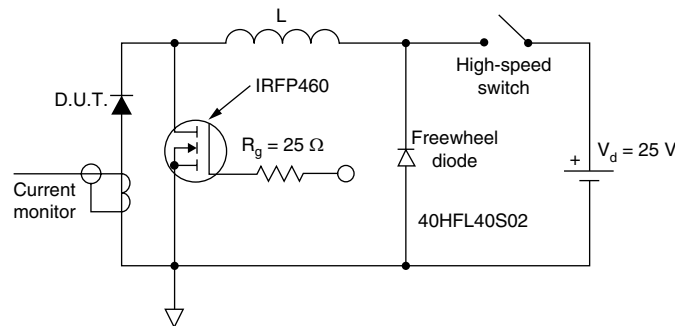


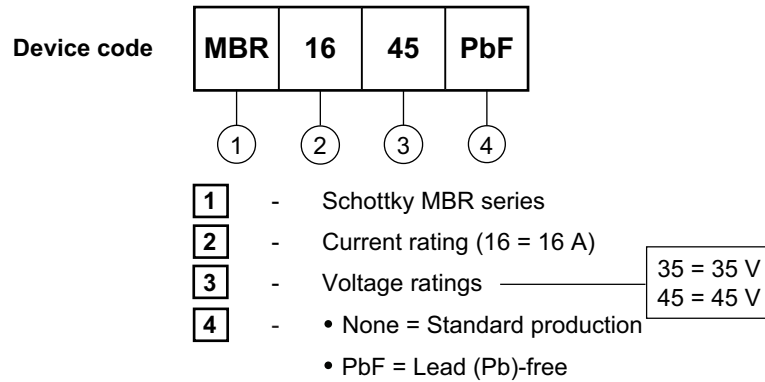
Fig. 8 - Unclamped Inductive Test Circuit

**Note**

- (1) Formula used:  $T_C = T_J - (P_d + P_{d_{REV}}) \times R_{thJC}$ ;  
 $P_d = \text{Forward power loss} = I_{F(AV)} \times V_{FM} \text{ at } (I_{F(AV)}/D)$  (see fig. 6);  
 $P_{d_{REV}} = \text{Inverse power loss} = V_{R1} \times I_R (1 - D)$ ;  $I_R$  at  $V_{R1} = \text{Rated } V_R$  applied



## ORDERING INFORMATION TABLE



LINKS TO RELATED DOCUMENTS	
Dimensions	<a href="http://www.vishay.com/doc?95221">http://www.vishay.com/doc?95221</a>
Part marking information	<a href="http://www.vishay.com/doc?95224">http://www.vishay.com/doc?95224</a>



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